



Shantou Huashan Electronic Devices Co.,Ltd.

PNP DIGITAL TRANSISTOR

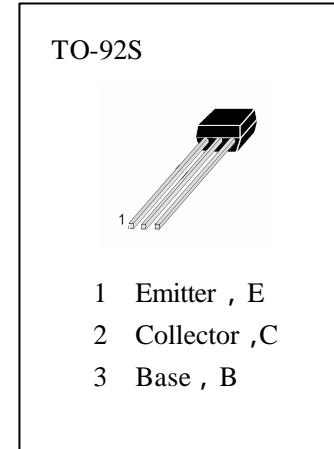
HA114Y

APPLICATIONS

Switching Circuit , Interface Circuit.

ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ C$)

T_{stg}	Storage Temperature.....	-55~150
T_j	Junction Temperature.....	150
P_c	Collector Dissipation.....	300mW
V_{CBO}	Collector-Base Voltage.....	-50V
V_{CEO}	Collector-Emitter Voltage.....	-50V
V_{EBO}	Emitter-Base Voltage.....	-6V
I_c	Collector Current.....	-100mA



ELECTRICAL CHARACTERISTICS ($T_a=25^\circ C$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
BV_{CBO}	Collector-Base Breakdown Voltage	-50			V	$I_C=-10 \mu A, I_E=0$
BV_{CEO}	Collector-Emitter Breakdown Voltage	-50			V	$I_C=-1mA, I_B=0$
I_{CBO}	Collector Cut-off Current			-0.1	μA	$V_{CB}=-40V, I_E=0$
I_{CEO}	Collector Cut-off Current			-0.5	μA	$V_{CE}=-40V, I_B=0$
I_{EBO}	Emitter Cut-off Current	-67	-88	-125	μA	$V_{EB}=-5V, I_C=0$
HFE	DC Current Gain	30				$V_{CE}=-5V, I_C=-5mA$
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage		-0.1	-0.3	V	$I_C=-10mA, I_B=-0.5mA$
$V_I(\text{off})$	Input Off Voltage	-0.5	-0.7	-0.9	V	$V_{CE}=-5V, I_C=-0.1mA$
$V_I(\text{on})$	Input On Voltage	-1.0	-2.0	-4.0	V	$V_{CE}=-0.2V, I_C=-10mA$
R1	Input Resistor	7.0	10	13	Kohm	
R1/ R2	Resistor Ratio	0.193	0.213	0.234		
f _r	Current Gain-Bandwidth Product		250		MHz	$V_{CE}=-10V, I_C=-5mA$
C _{ob}	Output Capacitance		5.5		pF	$V_{CB}=-10V, f=1MHz$



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●Electrical characteristic curves

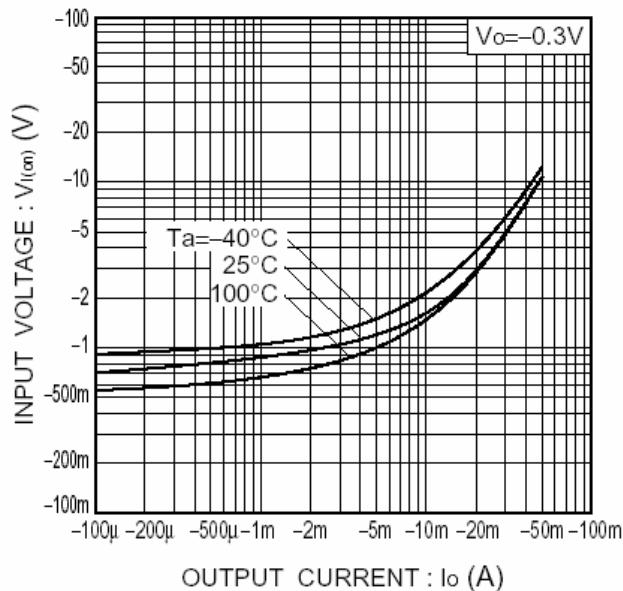


Fig.1 Input voltage vs. output current
(ON characteristics)

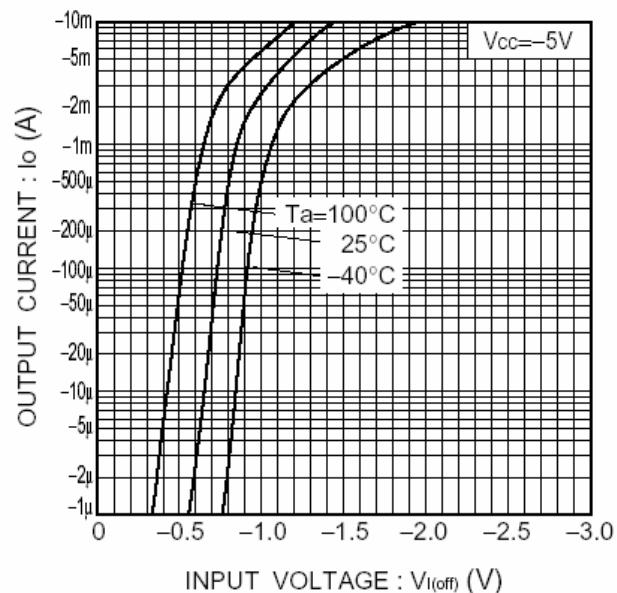


Fig.2 Output current vs. input voltage
(OFF characteristics)

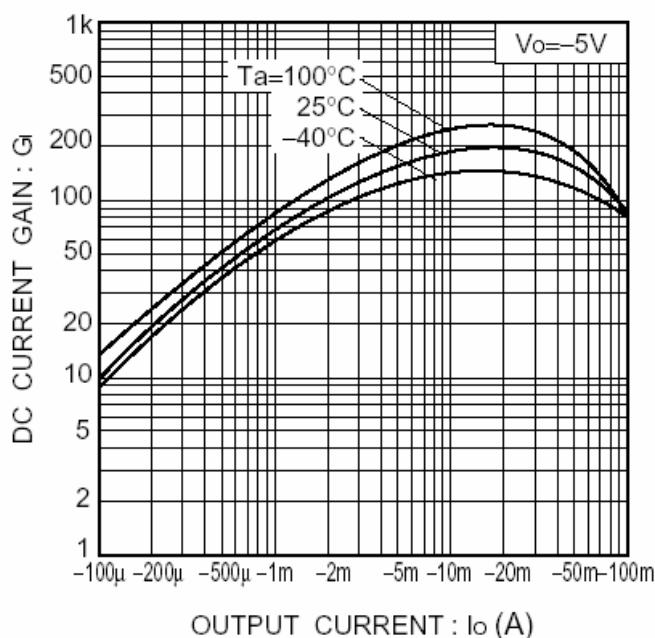


Fig.3 DC current gain vs. output current

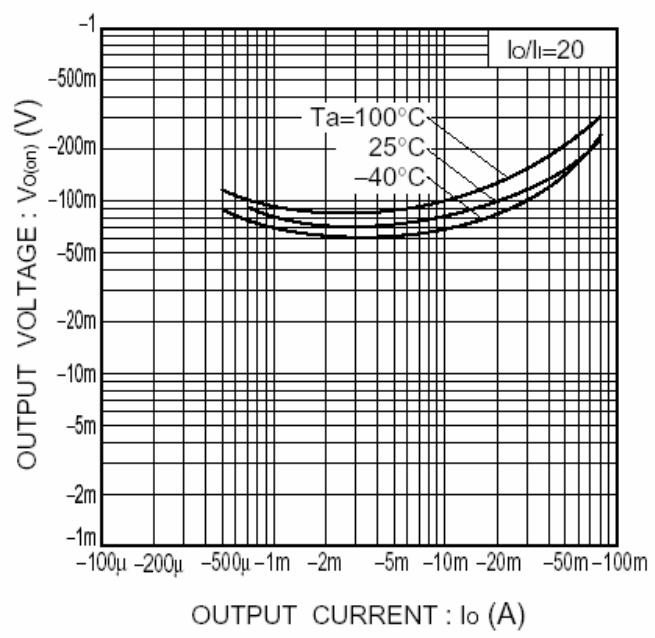


Fig.4 Output voltage vs. output current